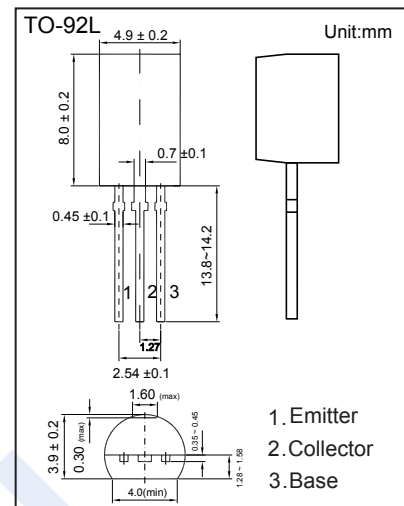


PNP Transistors

KTA1070

■ Features

- Low collector output capacitance
- High voltage and High f_T
- Complementary to KTC3467

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-200	V
Collector - Emitter Voltage	V_{CE0}	-200	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-100	mA
Collector Current - Pulse	I_{CP}	-200	
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100\mu\text{A}$, $I_E = 0$	-200			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1\text{ mA}$, $I_B = 0$	-200			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100\mu\text{A}$, $I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -150\text{V}$, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{ V}$, $I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20\text{mA}$, $I_B = -2\text{mA}$			-0.6	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -20\text{mA}$, $I_B = -2\text{mA}$			-1	
DC current gain	h_{FE}	$V_{CE} = -5\text{V}$, $I_C = -10\text{mA}$	70		240	
Reverse transfer capacitance	C_{re}	$V_{CB} = -30\text{V}$, $f = 1\text{MHz}$		1.7		pF
Collector output capacitance	C_{ob}	$V_{CB} = -30\text{V}$, $f = 1\text{MHz}$		2.6		
Transition frequency	f_T	$V_{CE} = -30\text{V}$, $I_C = -10\text{mA}$		150		MHz

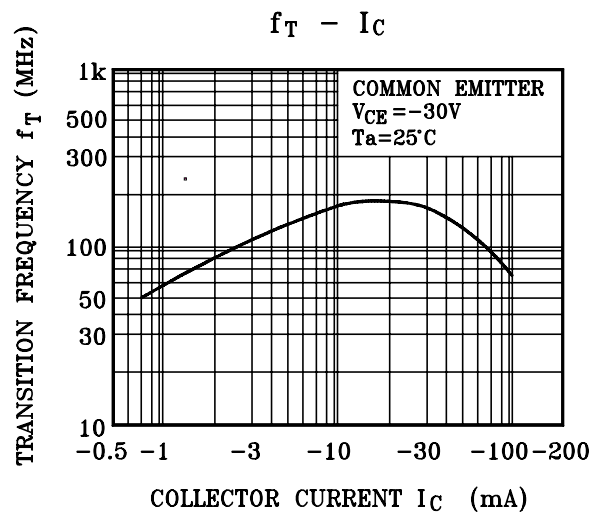
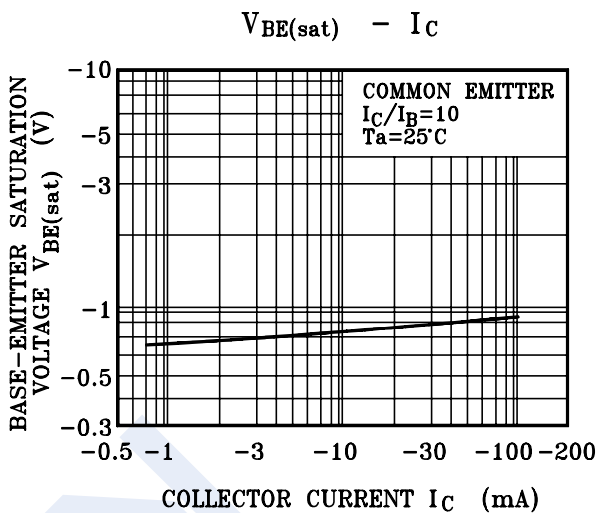
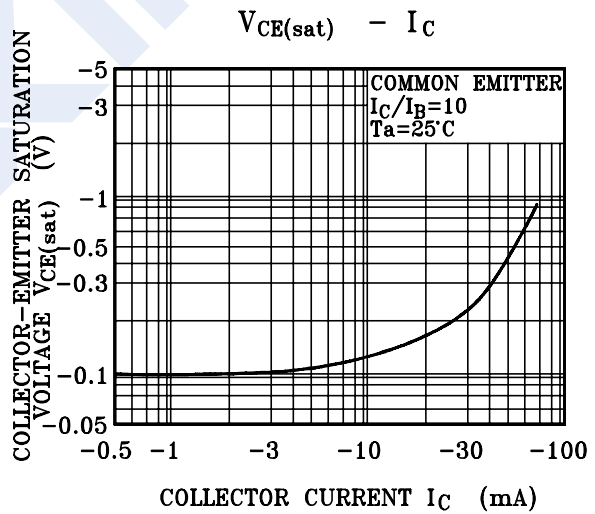
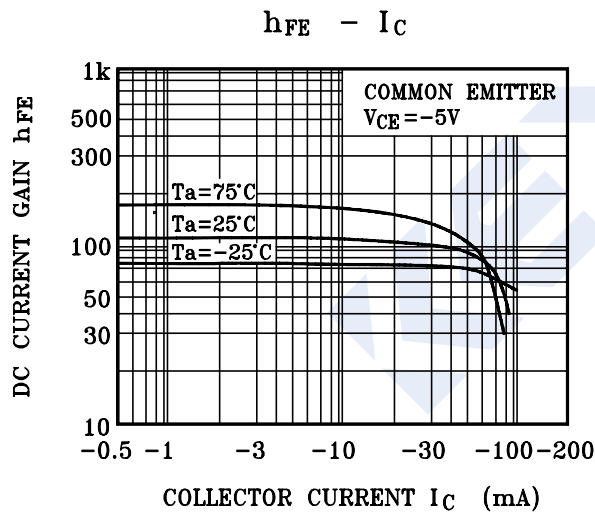
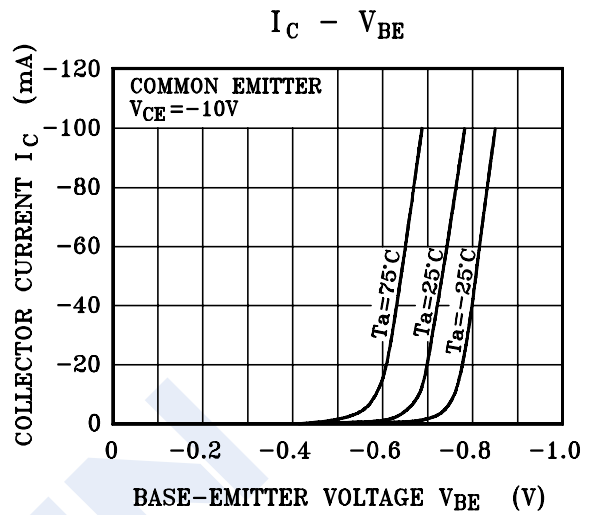
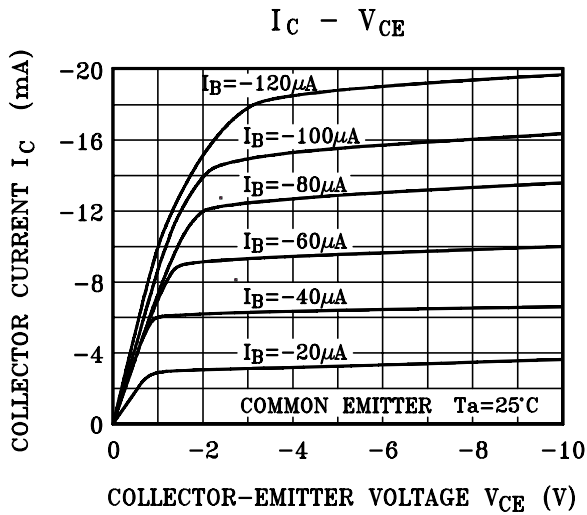
■ Classification of h_{FE}

Type	KTA1070-O	KTA1070-Y
Range	70-140	120-240

PNP Transistors

KTA1070

■ Typical Characteristics



PNP Transistors

KTA1070

■ Typical Characteristics

